

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

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Title of Invention	STRUCTURE AND METHOD OF FORMING BIPOLAR TRANSISTOR HAVING A SELF-ALIGNED RAISED EXTRINSIC BASE USING SELF-ALIGNED ETCH STOP LAYER
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Application Number :

Confirmation Number:

First Named Applicant: Marwan Khater

Attorney Docket Number: FIS920030412US1

Art Unit:

Examiner:

Search string: (5128271 or 5494836 or 5506427 or 5962880 or 6346453 or 6429085 or 6437376 or 6472262 or 6559020).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5128271	1992-07-07	Bronner, et al.			
	2	5494836	1996-02-27	Imai			
	3	5506427	1996-04-09	Imai			
	4	5962880	1999-10-05	Oda, et al.			
	5	6346453	2002-02-12	Kovacic, et al.			
	6	6429085	2002-08-06	Pinter			
	7	6437376	2002-08-20	Ozkan			
	8	6472262	2002-10-29	Chantre, et al.			
	9	6559020	2003-05-06	Salmi			

Signature

Examiner Name	Date